



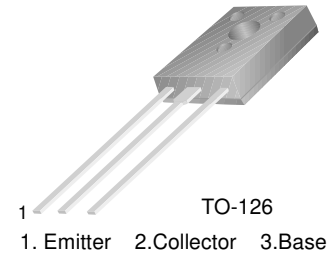
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BD234/236/238

Medium Power Linear and Switching Applications

- Complement to BD 233/235/237 respectively



PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage		
	: BD234	- 45	V
	: BD236	- 60	V
	: BD238	- 100	V
V_{CEO}	Collector-Emitter Voltage		
	: BD234	- 45	V
	: BD236	- 60	V
	: BD238	- 80	V
V_{CER}	Collector-Emitter Voltage		
	: BD234	- 45	V
	: BD236	- 60	V
	: BD238	- 100	V
V_{EBO}	Emitter-Base Voltage	- 5	V
I_C	Collector Current (DC)	- 2	A
I_{CP}	*Collector Current (Pulse)	- 6	A
P_C	Collector Dissipation ($T_C=25^\circ\text{C}$)	25	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature	- 65 ~ 150	$^\circ\text{C}$

Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
$V_{CEO(sus)}$	* Collector-Emitter Sustaining Voltage					
	: BD234	$I_C = - 100\text{mA}, I_B = 0$	- 45			V
	: BD236		- 60			V
	: BD238		- 80			V
I_{CBO}	Collector Cut-off Current					
	: BD234	$V_{CB} = - 45\text{V}, I_E = 0$			- 100	μA
	: BD236	$V_{CB} = - 60\text{V}, I_E = 0$			- 100	μA
	: BD238	$V_{CB} = - 100\text{V}, I_E = 0$			- 100	μA
I_{EBO}	Emitter Cut-off Current	$V_{EB} = - 5\text{V}, I_C = 0$			- 1	mA
h_{FE}	* DC Current Gain	$V_{CE} = - 2\text{V}, I_C = - 150\text{mA}$	40			
		$V_{CE} = - 2\text{V}, I_C = - 1\text{A}$	25			
$V_{CE(sat)}$	* Collector-Emitter Saturation Voltage	$I_C = - 1\text{A}, I_B = - 0.1\text{A}$			- 0.6	V
$V_{BE(on)}$	* Base-Emitter ON Voltage	$V_{CE} = - 2\text{V}, I_C = - 1\text{A}$			- 1.3	V
f_T	Current Gain Bandwidth Product	$V_{CE} = - 10\text{V}, I_C = - 250\text{mA}$	3			MHz

* Pulse Test: PW=300 μs , duty Cycle=1.5% Pulsed

Typical Characteristics

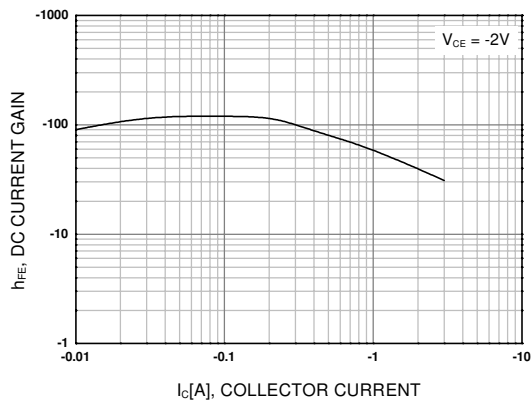


Figure 1. DC current Gain

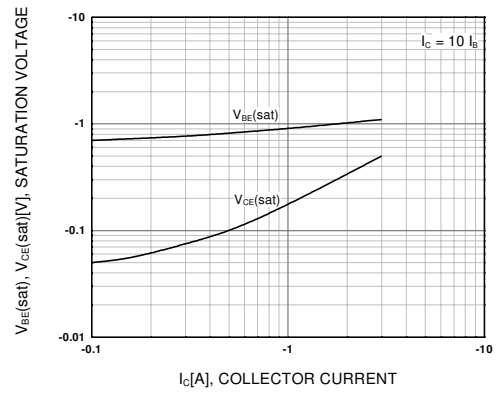


Figure 2. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

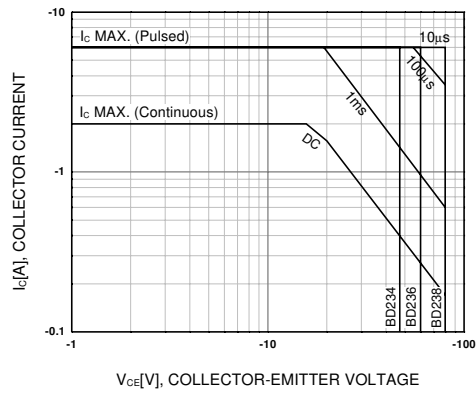


Figure 3. Safe Operating Area

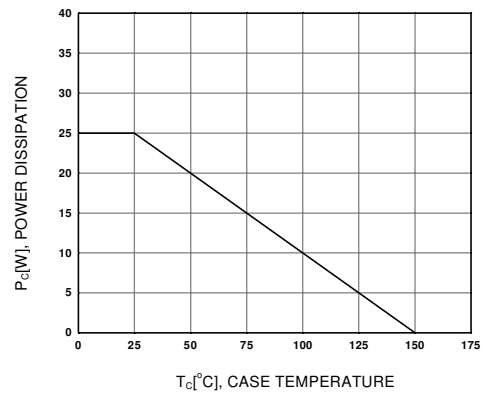
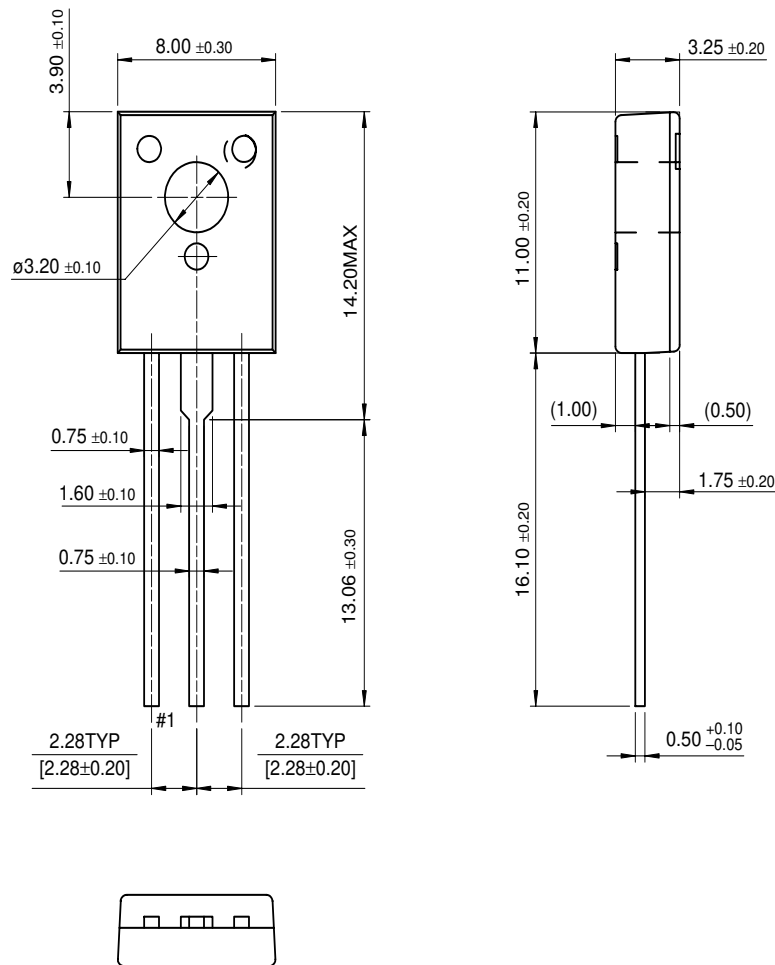


Figure 4. Power Derating

Package Dimensions

TO-126

BD234/236/238



Dimensions in Millimeters

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